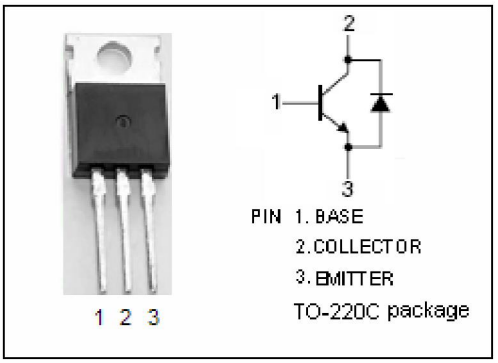
isc Silicon NPN Power Transistor BUL49D

DESCRIPTION

- Collector–Emitter Sustaining Voltage
  : $V_{CEO(SUS)}$ = 450V(Min.)
- Collector Saturation Voltage
  : $V_{CE(sat)}$ = 0.3V(Max) @ I_C= 1.0A
- Very High Switching Speed



APPLICATIONS

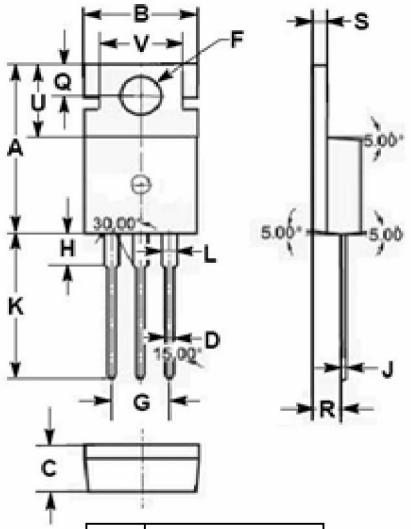
- Electronic transformers for halogen lamps
- Flyback and forward single transistor low power converters

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CES}	Collector-Emitter Voltage	850	V
V_{CEO}	Collector-Emitter Voltage	450	V
V_{EBO}	Emitter-Base Voltage	10	V
I_C	Collector Current-Continuous	5	A
I_{CM}	Collector Current-peak t_p<5ms	10	A
I_B	Base Current-Continuous	2	A
I_{BM}	Base Current-peak t_p<5ms	4	A
P_C	Collector Power Dissipation T_C=25℃	80	W
T_j	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-65~150	℃

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}c}$	Thermal Resistance,Junction to Case	1.56	℃/W
$R_{th\ j\text{-}A}$	Thermal Resistance,Junction to Ambient	62.5	℃/W



DIM	mm MIN	MAX
A	15.70	15.90
B	9.90	10.10
C	4.20	4.40
D	0.70	0.90
F	3.40	3.60
G	4.98	5.18
H	2.70	2.90
J	0.44	0.46
K	13.20	13.40
L	1.10	1.30
Q	2.70	2.90
R	2.50	2.70
S	1.29	1.31
U	6.45	6.65
V	8.66	8.86

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ELECTRICAL CHARACTERISTICS

T_C =25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	I_C= 10mA; L= 25mH	450			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	I_E= 10mA; I_C= 0	10		18	V
$V_{CE(sat)-1}$	Collector-Emitter Saturation Voltage	I_C= 1A; I_B= 0.2A			0.3	V
$V_{CE(sat)-2}$	Collector-Emitter Saturation Voltage	I_C= 2A; I_B= 0.4A			0.6	V
$V_{CE(sat)-3}$	Collector-Emitter Saturation Voltage	I_C= 4A; I_B= 0.8A			1.2	V
$V_{BE(sat)-1}$	Base-Emitter Saturation Voltage	I_C= 1A; I_B= 0.2A			1.0	V
$V_{BE(sat)-2}$	Base-Emitter Saturation Voltage	I_C= 4A; I_B= 0.8A			1.3	V
I_{CES}	Collector Cutoff Current	V_{CE}= 850V; V_{BE}= 0 V_{CE}= 850V; V_{BE}= 0, T_C= 125℃			0.1 0.5	mA
I_{EBO}	Emitter Cutoff Current	V_{EB}= 9V; I_C= 0			0.1	mA
h_{FE-1}	DC Current Gain	I_C= 10mA; V_{CE}= 5V	10			
h_{FE-2}	DC Current Gain	I_C= 0.5A; V_{CE}= 5V			60	
h_{FE-3}	DC Current Gain	I_C= 7A; V_{CE}= 10V	4		10	
V_F	Diode Forward Voltage	I_C= 3A			1.5	V
Switching Times, Resistive Load						
t_s	Storage Time	I_C= 2A; V_{CC}= 250V; I_{B1}= -I_{B2}= 0.4A			3	μs
t_f	Fall Time				0.8	μs
Switching Times, Inductive Load						
t_s	Storage Time	I_C= 4A; I_{B1}= 0.8A $V_{BE(off)}$= -5V; R_{BB}= 0Ω V_{CL}= 300V; L= 1mH			1.3	μs
t_f	Fall Time				0.1	μs